

# BA892WT

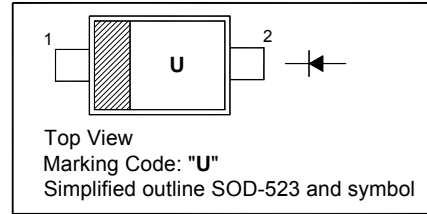
## SILICON BAND SWITCHING DIODE

### Applications

for band switching in VHF television tuners and surface mount band switching circuits

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

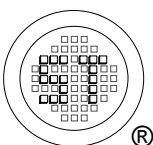


### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Current	$I_F$	100	mA
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Operating Temperature Range	$T_{op}$	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Current at $V_R = 20\text{ V}$	$I_R$	-	-	20	nA
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	-	-	1	V
Diode Capacitance at $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$ at $V_R = 3\text{ V}$ , $f = 1\text{ MHz}$ at $V_R = 0\text{ V}$ , $f = 100\text{ MHz}$	$C_T$	0.65 0.6 -	- - 1	1.4 1.1 -	pF
Forward Resistance at $I_F = 3\text{ mA}$ , $f = 100\text{ MHz}$ at $I_F = 10\text{ mA}$ , $f = 100\text{ MHz}$	$r_f$	- -	- -	0.7 0.5	$\Omega$
Series Inductance	$L_s$	-	0.6	-	nH



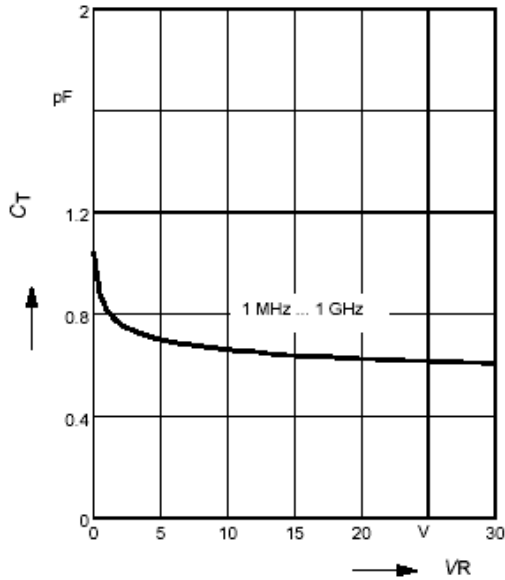
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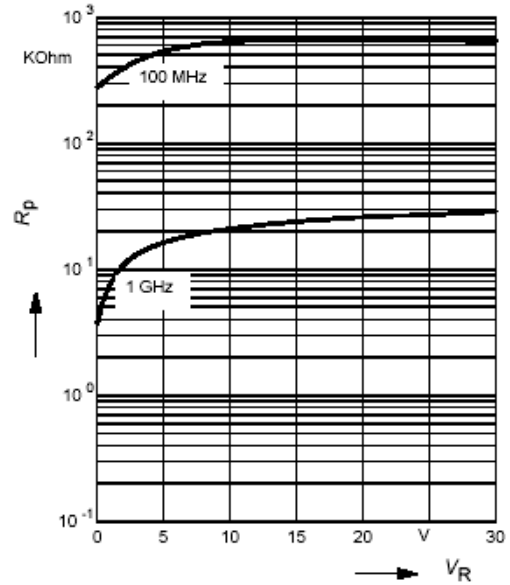
Diode capacitance  $C_T = f(V_R)$

$f =$  Parameter



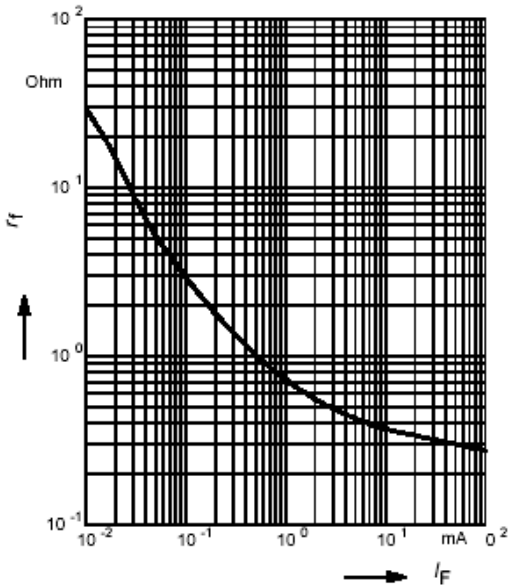
Reverse parallel resistance  $R_p = f(V_R)$

$f =$  Parameter



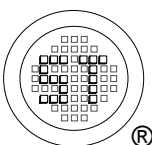
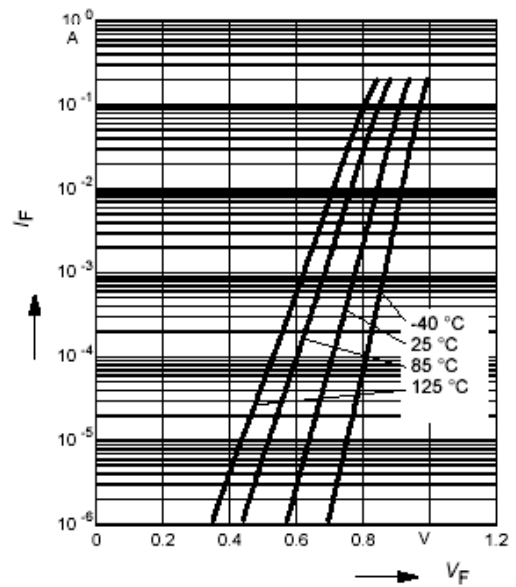
Forward resistance  $r_f = f(I_F)$

$f = 100\text{MHz}$



Forward current  $I_F = f(V_F)$

$T_A =$  Parameter



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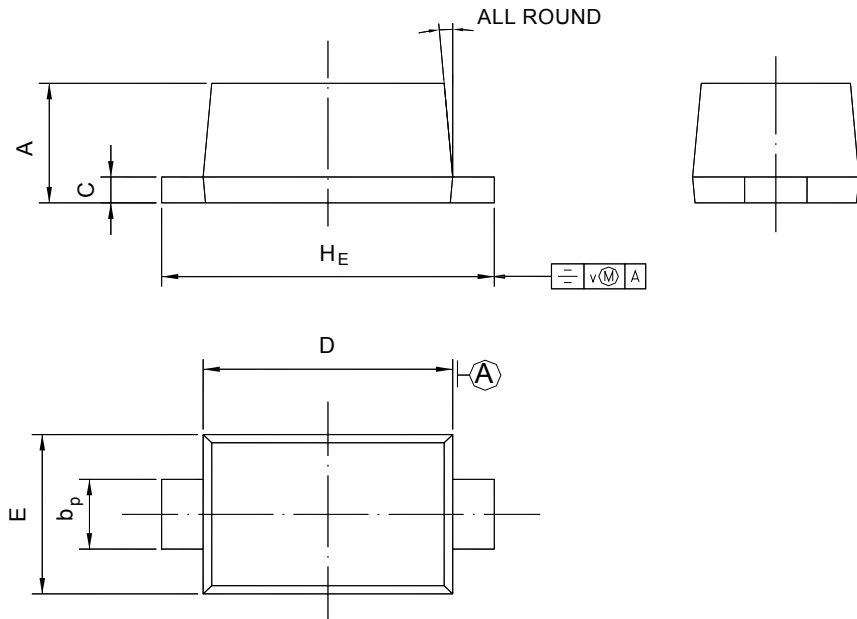


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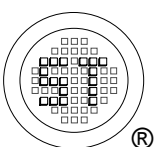
## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	V	
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°



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